

# **BC636 PNP Epitaxial Silicon Transistor**

# **Switching and Amplifier Applications**

Complement to BC635



## Absolute Maximum Ratings T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CER</sub>	Collector-Emitter Voltage at R <sub>BE</sub> =1KΩ	-45	V
V <sub>CES</sub>	Collector-Emitter Voltage	-45	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-45	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current	-1	A
I <sub>CP</sub>	Peak Collector Current	-1.5	A
I <sub>B</sub>	Base Current	-100	mA
P <sub>C</sub>	Collector Power Dissipation	1	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-65 ~ 150	°C

# Electrical Characteristics $T_a = 25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA, I <sub>B</sub> =0	-45			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = -30V, I <sub>E</sub> =0			-0.1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = -5V, I <sub>C</sub> =0			-0.1	μΑ
h <sub>FE1</sub> h <sub>FE2</sub> h <sub>FE3</sub>	DC Current Gain	V <sub>CE</sub> = -2V, I <sub>C</sub> = -5mA V <sub>CE</sub> = -2V, I <sub>C</sub> = -150mA V <sub>CE</sub> = -2V, I <sub>C</sub> = -500mA	25 40 25		250	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA			-0.5	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> = -2V, I <sub>C</sub> = -500mA			-1	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA, f=50MHz		100		MHz

# **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
BC636	BC636BU	TO-92			10,000
BC636	BC636TA	TO-92			2,000
BC636	BC636TAR	TO-92			2,000
BC636	BC636TF	TO-92			2,000
BC636	BC636TFR	TO-92			2,000

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## **Typical Performance Characteristics**

Figure 1. Static Characteristic

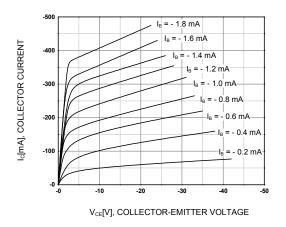


Figure 2. DC Current Gain

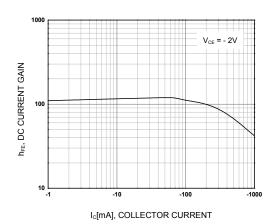
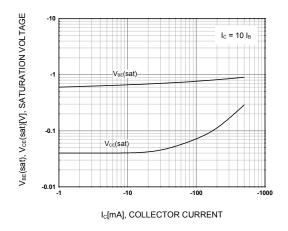
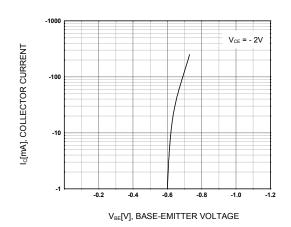


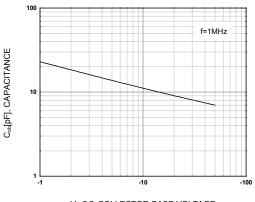
Figure 3. Base-Emitter Saturation Voltage **Collector-Emitter Saturation Voltage** 

Figure 4. Base-Emitter On Voltage





**Figure 5. Collector Output Capacitance** 



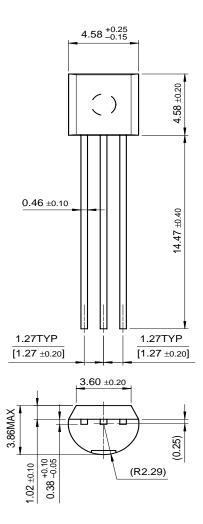
V<sub>CB</sub>[V], COLLECTOR-BASE VOLTAGE

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## **Mechanical Dimensions**

TO-92





Dimensions in Millimeters

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DOME™	HiSeC™	MSX™	RapidConfigure™	UltraFET <sup>™</sup>
EcoSPARK™	I <sup>2</sup> C™	MSXPro™	RapidConnect™	UniFET <sup>™</sup>
E <sup>2</sup> CMOS™	<i>i-Lo</i> ™	OCX™	µSerDes™	VCX <sup>™</sup>
EnSigna™	ImpliedDisconnect™	OCXPro™	SILENT SWITCHER <sup>®</sup>	Wire™
FACT™	IntelliMAX™	OPTOLOGIC <sup>®</sup>	SMART START™	

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